

LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)		ATTY. DOCKET NO. Y0996-118X		SERIAL NO.		
		APPLICANT: Kevin K. Chan et al.				
		FILING DATE: HEREWITH		GROUP:		
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Examiner Initial	Document Number	Date	Name	Class	Sub-Class	Filing Date
AA	5,405,787	04/95	Kazumi Kurimoto	H01L	21/265	10/14/93
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AL	JP 06-350085	12/94	Japan	H01L	29/784	Abstract
AM	JP 04-180633	06/92	Japan	H01L	21/336	Abstract
AN	TW 266313	12/95	Taiwan			Abstract
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AR	A. Acovic et al., "Novel Gate Process for 0.1 Micron MOSFETs",					
	IBM Technical Disclosure Bulletin, Vol. 36, No. 11, November 1993.					
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EXAMINER		DATE CONSIDERED				
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